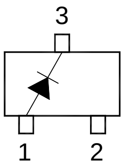
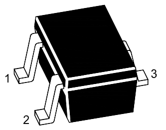
SDB127W

Silicon Epitaxial Planar Schottky Barrier Diode

Features

- Low forward voltage
- Allowing high density mounting





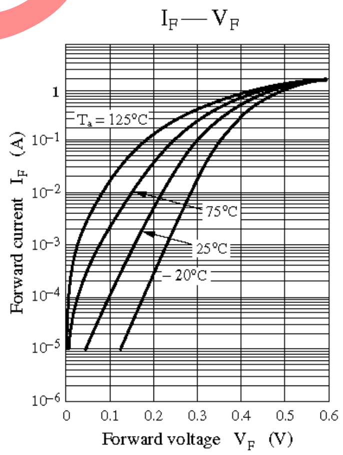
SOT-323 Plastic Package
Marking Code: **YR**

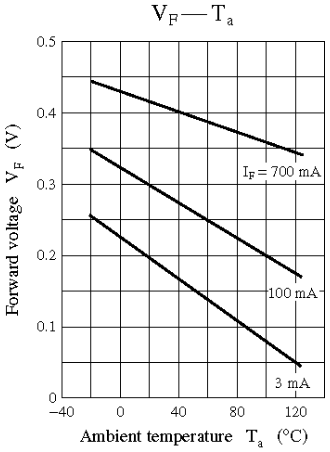
Absolute Maximum Ratings (T_a = 25℃)

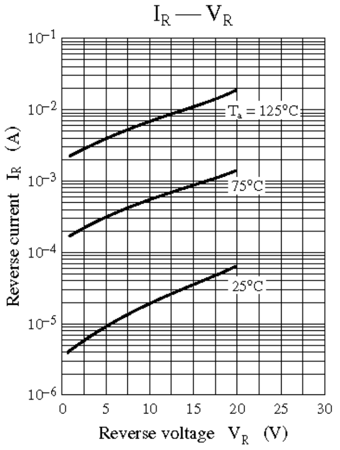
Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	25	V
Reverse Voltage	V_R	20	V
Average Forward Current	$I_{F(AV)}$	700	mA
Non-repetitive Peak Forward Surge Current (t = 8.3 ms)	I_{FSM}	2	A
Junction Temperature	T_J	125	℃
Storage Temperature Range	T_{stg}	- 55 to + 125	℃

Characteristics at T_a = 25℃

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at I_F = 700 mA	V_F	-	0.45	V
Reverse Current at V_R = 20 V	I_R	-	200	µA
Reverse Breakdown Voltage at I_R = 600 µA	$V_{(BR)R}$	25	-	V
Junction Capacitance at V_R = 0, f = 1 MHz	C_J	-	100	pF







SEMTECH ELECTRONICS LTD.
Subsidiary of Sino-Tech International (BVI) Limited

ISO/TS 16949 : 2009 Certificate No. M-2012-0062
ISO14001 : 2004 Certificate No. 7116
ISO 9001 : 2008 Certificate No. 0506098
BS-OHSAS 18001 : 2007 Certificate No. 7116
IECQ QC 080000 Certificate No. PRC-HSPM-1483-1

Dated : 07/06/2013 Rev : 01